

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Masato HIRAMATSU, et al.

SERIAL NO: New Application

GAU:

FILED: Herewith

EXAMINER:

FOR: SEMICONDUCTOR STRUCTURE, SEMICONDUCTOR DEVICE, AND METHOD AND APPARATUS FOR
MANUFACTURING THE SAME

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

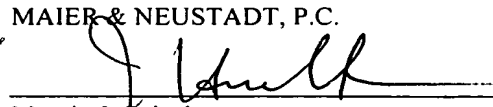
- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 246036US2		SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Masato HIRAMATSU, et al.			
				FILING DATE Herewith		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AK	2002-289865	10/04/2002	JAPAN (with English Abstract)			X
	AL						
	AM						
	AN						
	AO						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AP	Shinya TSUDA, et al., "PREPARATION AND PROPERTIES OF HIGH-QUALITY a-Si FILMS WITH A SUPER CHAMBER (SEPARATED ULTRA-HIGH VACUUM REACTION CHAMBER)", Japanese Journal of Applied Physics, Vol. 26, No. 1, January 1987, pgs. 33-38					
	AQ	C. C. TSAI, et al., "'CLEAN' a-Si:H PREPARED IN A UHV SYSTEM", Journal of Non-Crystalline Solids, Vol. 66, 1984, pgs. 45-50					
	AR	Masato HIRAMATSU, et al., "AN ADVANCED PECVD SYSTEM FOR MASS-PRODUCING HIGH-PURITY Si THIN FILMS", IDW '02 Proceedings of the Ninth International Display Workshops, December 4-6, 2002, 2 pgs					
	AS	Masato HIRAMATSU, et al., "MECHANISM OF OXYGEN CONTAMINATION IN PECVD A-SI:H FILMS", Electrochemical Society Proceedings Volume 2003-08, pgs. 701-707					
	AT	Toshihiro KAMEI, et al., "DEPOSITION OF ULTRAPURE HYDROGENATED AMORPHOUS SILICON", J. Vac. Sci. Technol. A, Vol. 17, No. 1, Jan/Feb 1999, pgs. 113-120					
	AU	U. KROLL, et al., "ORIGINS OF ATMOSPHERIC CONTAMINATION IN AMORPHOUS SILICON PREPARED BY VERY HIGH FREQUENCY (70 MHz) GLOW DISCHARGE", J. Vac. Sci. Technol. A, Vol. 13, No. 6, Nov/Dec 1995, pgs. 2742-2746					
	AV	A. A. HOWLING, et al., "FREQUENCY EFFECTS IN SILANE PLASMAS FOR PLASMA ENHANCED CHEMICAL VAPOR DEPOSITION", J. Vac. Sci. Technol. A, Vol. 10, No. 4, Jul/Aug 1992, pgs. 1080-1085				<input type="checkbox"/> Additional References sheet(s) attached	
Examiner							
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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STATEMENT OF RELEVANCY

Reference AK (JP 2002-289865) on PTO Form 1449:

This reference is discussed in the specification.